

**Out of Stock - Product is not available at this time - Boron implant in silicon - Depth profile**

Art. ID                      NIST-2137  
Unit                         each  
Deliverydetails            No Dangerous Good /not restricted

Description

This Standard Reference Material (SRM®) is intended for use in calibrating the secondary ion response to minor and trace levels of boron in a silicon matrix by the analytical technique of secondary ion mass spectrometry (SIMS). A unit of NIST-2137 consists of a single crystal silicon substrate with a surface rendered disordered by silicon ion implantation. The substrate is ion-implanted with the isotope 10B at a nominal energy of 50 keV. NIST-2137 is certified for the retained dose of 10B atoms by neutron depth profiling. The dose is expressed in units of 10B mass per unit area. Noncertified information about the concentration of 10B atoms as a function of depth below the surface is provided by SIMS. /// Sample value(s) - please ask for current certificate.

| Text/Information | Analyte/Parameter    | CAS number | Concentration/Value | Unit               | Method | Source |
|------------------|----------------------|------------|---------------------|--------------------|--------|--------|
|                  | Retained dose of 10B |            | 0,01692 ± 0.00059   | µg/cm <sup>2</sup> |        |        |